

**Amendments to show changes made
(Additions in bold, deletions in bold brackets)**

Claims 1 and 7:

1. (Amended) A semiconductor bridge (SCB) device, comprising:
a laminate layer on top of an insulating material, wherein the laminate layer comprises a series of layers of at least two reactive materials, and wherein the laminate layer comprises,
two relatively large sections that substantially cover the surface area of the insulating material, and
a bridge section joining the two relatively large sections;
for each of the two relatively large sections, at least one conductive contact pad coupled to at least one of the series of layers of that relatively large section, wherein a predetermined current between [through the] at least one conductive contact pad on one of the relatively large sections and at least one conductive pad on the other of the relatively large sections causes the bridge section to initiate a reaction in which the laminate layer is involved.
7. (Amended) The SCB device of claim 1, wherein the [at least one] conductive contact pads comprise [pad comprises] titanium, nickel and gold.